

AS7C34096A-8TIN 512K X 8 BIT HIGH SPEED CMOS SRAM

REVISION HISTORY

Revision	<u>Description</u>	Issue Date
Rev. 1.0	Initial Issue	July.12. 2012
Rev. 1.1	."CE# \ge V _{CC} - 0.2V" revised as "CE# \le 0.2" for TEST CONDITION of Average Operating Power supply Current lcc1 on page3	July.19. 2012
Rev.1.2	Add "Green package available" on page 1	Nov. 02. 2012
Rev.1.3	1.Revise "TEST CONDITION" for VOH, VOL on page 3 loH = -8mA revised as -4mA loL =4mA revised as 8mA 2. Revise VIH(max) & VIL(min) note on page 3 VIH(max) = VCC + 2.0V for pulse width less than 6ns. VIL(min) = VSS - 2.0V for pulse width less than 6ns.	June. 04. 2013



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FEATURES

■ Fast access time: 8ns

■ Low power consumption:

Operating current: 50mA(TYP.) Standby current: 2mA(TYP.)

■ Single 3.3V power supply

■ All inputs and outputs TTL compatible

■ Fully static operation

■ Temperature range - Industrial -40°~85°C

■ Tri-state output

■ Green package/ROHS compliant (N)

■ Data retention voltage : 1.5V (MIN.)

■ Package: 44-pin 400 mil TSOP-II

GENERAL DESCRIPTION

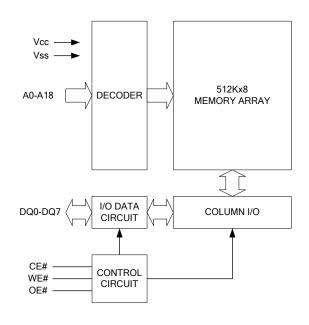
The AS7C34096A is a 4,194,304-bit high speed CMOS static random access memory organized as 524,288 words by 8 bits. It is fabricated using very high performance, high reliability CMOS technology. Its standby current is stable within the range of operating temperature.

The AS7C34096A operates from a single power supply of 3.3V and all inputs and outputs are fully TTL compatible

PRODUCT FAMILY

Product	Operating	Voc Bango	Speed	Power [Dissipation
Family	Temperature	Vcc Range	Speed	Standby(IsB1,TYP.)	Operating(Icc1,TYP.)
AS7C34096A(I)	-40° ~ 85℃	3.0 ~ 3.6V	8ns	2mA	50mA

FUNCTIONAL BLOCK DIAGRAM



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 - A18	Address Inputs
DQ0 – DQ7	Data Inputs/Outputs
CE#	Chip Enable Inputs
WE#	Write Enable Input
OE#	Output Enable Input
Vcc	Power Supply
Vss	Ground
NC	No Connection



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PIN CONFIGURATION

1				1
NC	1		44	NC
NC	2		43	NC
A4	3		42	□ NC
A3	4		41	A5
A2	5		40	A6
A1	6		39	A7
A0	7		38	A8
CE#	8	\triangleright	37	OE#
DQ0	9	\mathcal{S}	36	DQ7
DQ1	10	$\sim \sim \sim$	35	DQ6
Vcc	11	\diamond \diamond \otimes	34	Vss
Vss	12	$\stackrel{\sim}{4} \bigcirc \bigcirc$	33	Vcc
DQ2	13	$\mathcal{S}\mathcal{S}\mathcal{S}$	32	DQ5
DQ3	14	34096 XXX	31	DQ4
WE#	15	Ď	30	A9
A18	16		29	A10
A17	17		28	A11
A16	18		27	A12
A15	19		26	A13
A14	20		25	NC
NC	21		24	NC
NC	22		23	□ NC
				J

TSOP-II

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ABSOLUTE MAXIMUM RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Voltage on Vcc relative to Vss	V _{T1}	-0.5 to 4.6	V
Voltage on any other pin relative to Vss	VT2	-0.5 to Vcc+0.5	V
Operating Temperature	Та	-40 to 85(I grade)	$^{\circ}$
Storage Temperature	Тѕтс	-65 to 150	°C
Power Dissipation	PD	1	W
DC Output Current	Іоит	50	mA

^{*}Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

TRUTH TABLE

MODE	CE#	OE#	WE#	I/O OPERATION	SUPPLY CURRENT
Standby	Н	Х	X	High-Z	ISB,ISB1
Output Disable	L	Н	Н	High-Z	Icc,Icc1
Read	L	L	Н	Dout	lcc,lcc1
Write	L	Х	L	Din	lcc,lcc1

Note: $H = V_{IH}$, $L = V_{IL}$, X = Don't care.

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	l	MIN.	TYP. *4	MAX.	UNIT
Supply Voltage	Vcc		-8	3.0	3.3	3.6	V
Input High Voltage	V _{IH} ^{*1}			2.2	-	V _{CC} +0.3	V
Input Low Voltage	V _{IL} *2			- 0.3	-	0.8	V
Input Leakage Current	ILI	V _{CC} ≧ V _{IN} ≧ V _{SS}		- 1	-	1	μA
Output Leakage Current	ILO	Vcc ≧ Vouт ≧ Vss, Output Disabled	,		-	1	μΑ
Output High Voltage	Vон	он = -4mA		2.4	-	-	V
Output Low Voltage	Vol	I _{OL} = 8mA	ol = 8mA		-	0.4	V
Average Operating Power supply Current	Icc	Cycle time = Min. CE# = V _{IL} , I _{I/O} = 0mA, Others at V _{IL} or V _{IH}	-8	-	65	80	mA
Average Operating Power supply Current	lcc1	CE# \leq 0.2, Others at 0.2V or Vcc-0.2V I _{I/O} = 0mA;f=max	-8	-	50	60	mA
Standby Dower	Isa	CE# =V _{IH} , Others at V _{IL} or '	ViH	-	-	30	mA
Standby Power Supply Current	I _{SB1}	CE# \geq V _{CC} - 0.2V, Others at 0.2V or V _{CC} - 0.2V	V	-	2	10	mA

Notes:

- 1. VIH(max) = Vcc + 2.0V for pulse width less than 6ns.
- 2. V_{IL}(min) = V_{SS} 2.0V for pulse width less than 6ns.
- 3. Over/Undershoot specifications are characterized on engineering evaluation stage, not for mass production test.
- 4. Typical values are included for reference only and are not guaranteed or tested. Typical valued are measured at V_{CC} = V_{CC}(TYP.) and T_A = 25°C

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CAPACITANCE (TA = 25°C, f = 1.0MHz)

PARAMETER	SYMBOL	MIN.	MAX	UNIT
Input Capacitance	Cin	-	8	pF
Input/Output Capacitance	CI/O	-	10	pF

Note: These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Speed	8ns
Input Pulse Levels	0.2V to Vcc - 0.2V
Input Rise and Fall Times	3ns
Input and Output Timing Reference Levels	1.5V
Output Load	$C_L = 30pF + 1TTL$, $I_{OH}/I_{OL} = -4mA/8mA$

AC ELECTRICAL CHARACTERISTICS

(1) READ CYCLE

_				
PARAMETER	SYM.	AS7C34	1096A-8	UNIT
FANAIVILILIX	STW.	MIN.	MAX.	ONT
Read Cycle Time	trc	8	-	ns
Address Access Time	t AA	-	8	ns
Chip Enable Access Time	t ACE	-	8	ns
Output Enable Access Time	toe	-	4.5	ns
Chip Enable to Output in Low-Z	tclz*	2	-	ns
Output Enable to Output in Low-Z	tolz*	0	-	ns
Chip Disable to Output in High-Z	tcнz*	-	3	ns
Output Disable to Output in High-Z	tonz*	-	3	ns
Output Hold from Address Change	tон	2	-	ns

(2) WRITE CYCLE

PARAMETER	SYM.	AS7C34	1096A-8	UNIT
FARAMETER	STIVI.	MIN.	MAX.	ONT
Write Cycle Time	twc	8	-	ns
Address Valid to End of Write	taw	6.5	-	ns
Chip Enable to End of Write	tcw	6.5	-	ns
Address Set-up Time	tas	0	-	ns
Write Pulse Width	twp	6.5	-	ns
Write Recovery Time	twr	0	-	ns
Data to Write Time Overlap	tow	5	-	ns
Data Hold from End of Write Time	tон	0	-	ns
Output Active from End of Write	tow*	2	-	ns
Write to Output in High-Z	twnz*	-	3	ns

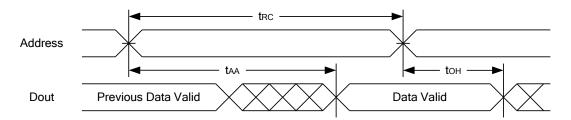
^{*}These parameters are guaranteed by device characterization, but not production tested.



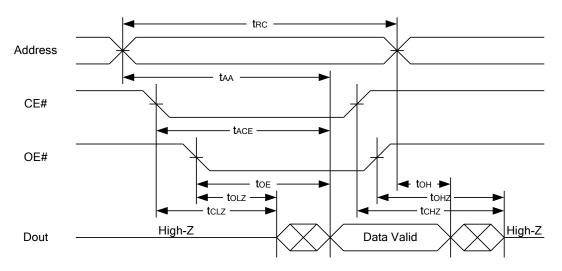
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TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2)



READ CYCLE 2 (CE# and OE# Controlled) (1,3,4,5)



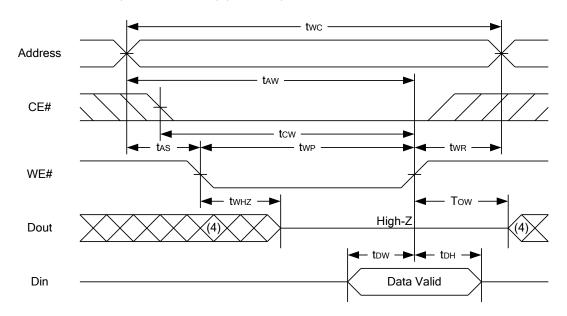
Notes:

- 1.WE# is high for read cycle.
- 2.Device is continuously selected OE# = low, CE# = low.
- 3.Address must be valid prior to or coincident with CE# = low,; otherwise tAA is the limiting parameter.
- 4.tclz, tolz, tchz and tohz are specified with CL = 5pF. Transition is measured ±500mV from steady state.
- 5.At any given temperature and voltage condition, tcHz is less than tcLz, toHz is less than toLz.

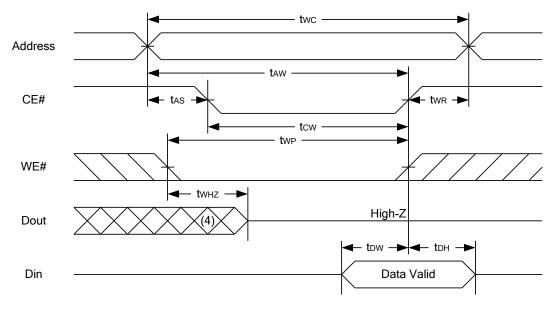


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WRITE CYCLE 1 (WE# Controlled) (1,2,3,5,6)



WRITE CYCLE 2 (CE# Controlled) (1,2,5,6)



Notes:

- 1.WE#, CE# must be high during all address transitions.
- 2.A write occurs during the overlap of a low CE#, low WE#.
- 3.During a WE# controlled write cycle with OE# low, twp must be greater than twHz + tpw to allow the drivers to turn off and data to be placed on the bus.
- 4. During this period, I/O pins are in the output state, and input signals must not be applied.
 5. If the CE# low transition occurs simultaneously with or after WE# low transition, the outputs remain in a high impedance state.
- 6.tow and twHz are specified with C_L = 5pF. Transition is measured ±500mV from steady state.



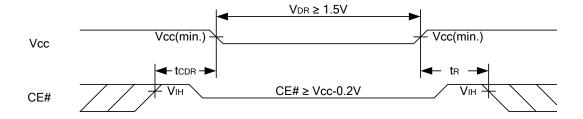
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DATA RETENTION CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Vcc for Data Retention	V_{DR}	CE# ≧ Vcc - 0.2V	1.5	-	3.6	V
Data Retention Current	ldr	Vcc = 1.5V CE# ≧ Vcc - 0.2V Others at 0.2V or Vcc – 0.2V	-	2	10	mA
Chip Disable to Data Retention Time	tcdr	See Data Retention Waveforms (below)	0	-	-	ns
Recovery Time	t _R		t _{RC*}	-	-	ns

t_{RC*} = Read Cycle Time

DATA RETENTION WAVEFORM



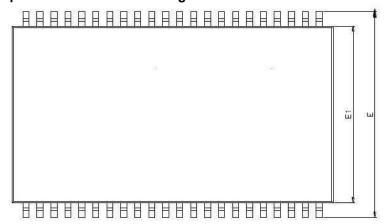


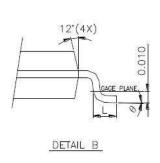
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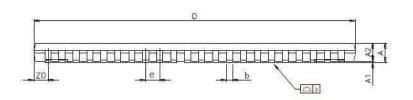
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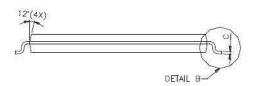
PACKAGE OUTLINE DIMENSION

44-pin 400mil TSOP-II Package Outline Dimension









SYMBOLS	DIMENSIONS IN MILLMETERS			DIMENSIONS IN MILS		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
Α	-	-	1.20	-	-	47.2
A1	0.05	0.10	0.15	2.0	3.9	5.9
A2	0.95	1.00	1.05	37.4	39.4	41.3
b	0.30	-	0.45	11.8	-	17.7
С	0.12	-	0.21	4.7	-	8.3
D	18.212	18.415	18.618	717	725	733
E	11.506	11.760	12.014	453	463	473
E1	9.957	10.160	10.363	392	400	408
е	-	0.800	-	-	31.5	-
L	0.40	0.50	0.60	15.7	19.7	23.6
ZD	ı	0.805	-	-	31.7	-
У	-	-	0.076	-	-	3
θ	0°	3°	6°	0°	3°	6°



AS7C34096A-8TIN 512K X 8 BIT HIGH SPEED CMOS SRAM

Rev. 1.3

ORDERING INFORMATION

Package Type	Access Time	Temperature	Packing	Alliance Memory
	(Speed)(ns)	Range(°C)	Type	Part No.
44Pin(400mil)	8	-40°C~85°C	Tray	AS7C34096A-8TIN
TSOP-II			Tape Reel	AS7C34096A-8TINTR



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